



**BLD NPN 系列晶体管/ BLD NPN SERIES TRANSISTORS**

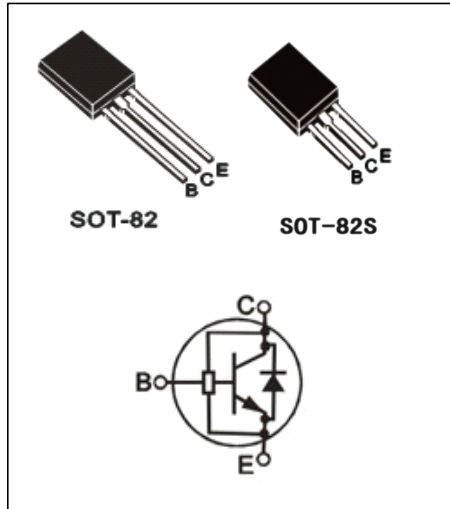
**BLD135DH**

- **特点:** 耐压高 开关速度快 安全工作区宽 符合 **RoHS** 规范
- **FEATURES:** ■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■RoHS COMPLIANT
- **应用:** 充电器 节能灯 电子镇流器
- **APPLICATION:** ■RECHARGER ■FLUORESCENT LAMP ■ELECTRONIC BALLAST

● **最大额定值 (Ta=25°C)**

● **Absolute Maximum Ratings (Ta=25°C) SOT-82/82S**

参数 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极-基极电压 Collector-Base Voltage	V <sub>CB0</sub>	850	V
集电极-发射极电压 Collector-Emitter Voltage	V <sub>CEO</sub>	450	V
集电极-发射极电压 Emitter- Base Voltage	V <sub>EBO</sub>	9.0	V
基极电流 Base Current	I <sub>b</sub>	1.0	A
集电极电流 Collector Current	I <sub>c</sub>	4.0	A
集电极耗散功率 Total Power Dissipation	P <sub>tot</sub>	1.3	W
最高工作温度 Junction Temperature	T <sub>j</sub>	150	°C
贮存温度 Storage Temperature	T <sub>stg</sub>	-65-150	°C



● **电特性 (Ta=25°C)**

● **Electronic Characteristics (Ta=25°C)**

参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =850V		100	μA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =450V, I <sub>B</sub> =0		250	μA
集电极-基极电压 Collector-Base Voltage	V <sub>CB0</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	850		V
集电极-发射极电压 Collector-Emitter Voltage	V <sub>CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	450		V
发射极-基极电压 Emitter- Base Voltage	V <sub>EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	9		V
集电极-发射极饱和电压 Collector-Emitter Saturation Voltage	V <sub>cesat</sub>	I <sub>C</sub> =0.5A, I <sub>B</sub> =0.1A		0.5	V
		I <sub>C</sub> =4.0A, I <sub>B</sub> =1.0A		1.5	V
发射极-基极饱和电压 Base-Emitter Saturation Voltage	V <sub>besat</sub>	I <sub>C</sub> =2.0A, I <sub>B</sub> =0.5A		1.6	V
电流放大倍数 DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	7		
		V <sub>CE</sub> =5V, I <sub>C</sub> =1A	20	30	
		V <sub>CE</sub> =5V, I <sub>C</sub> =4.0A	5		
贮存时间/Storage Time	t <sub>s</sub>	V <sub>CC</sub> =5V, I <sub>C</sub> =0.5A	2	4	μS
下降时间/Falling Time	t <sub>f</sub>	(UI9600)		0.8	μS
内置二极管正向压降 Diode Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =2.0A		2.6	V

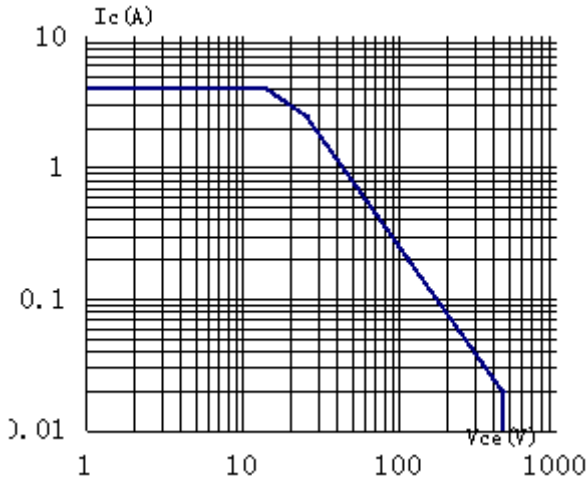
● **订单信息/ORDERING INFORMATION:**

包装形式/PACKING	订货编码/ORDERING CODE	
	普通塑封料 Normal Package Material	无卤塑封料 Halogen Free
SOT-82 普通袋装/NORMAL PACKING	BLD135DH SOT-82	BLD135DH SOT-82-HF
SOT-82S 普通袋装/NORMAL PACKING	BLD135DH SOT-82S	BLD135DH SOT-82S-HF

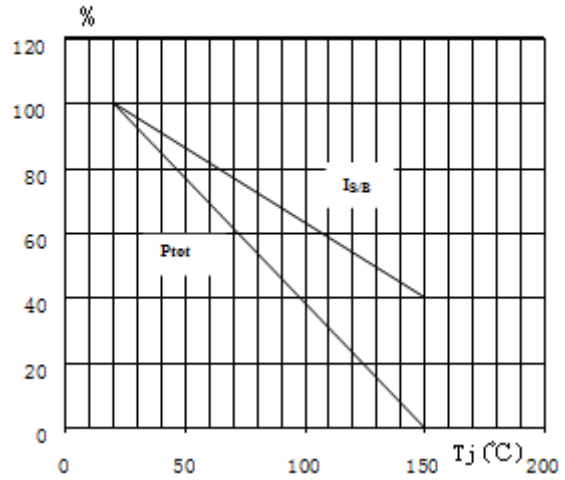
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BLD135DH

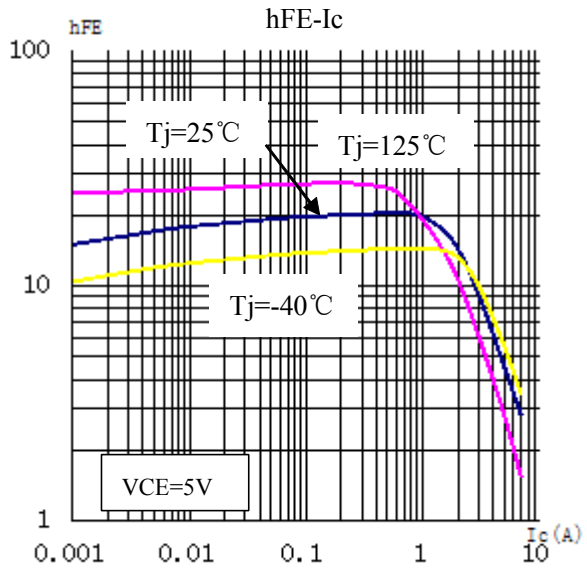
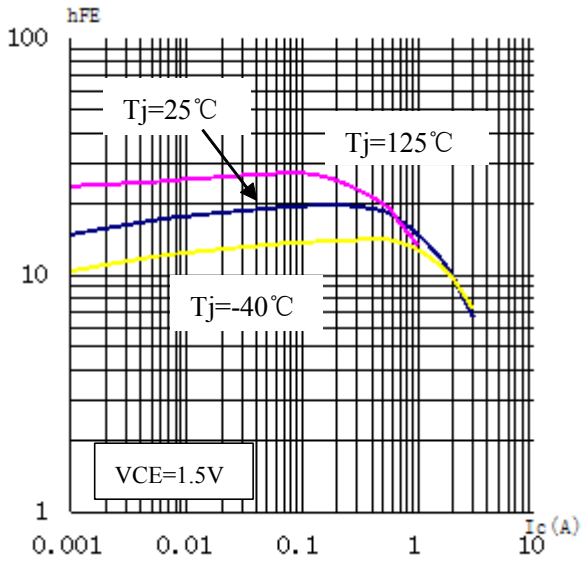
SOA (DC)



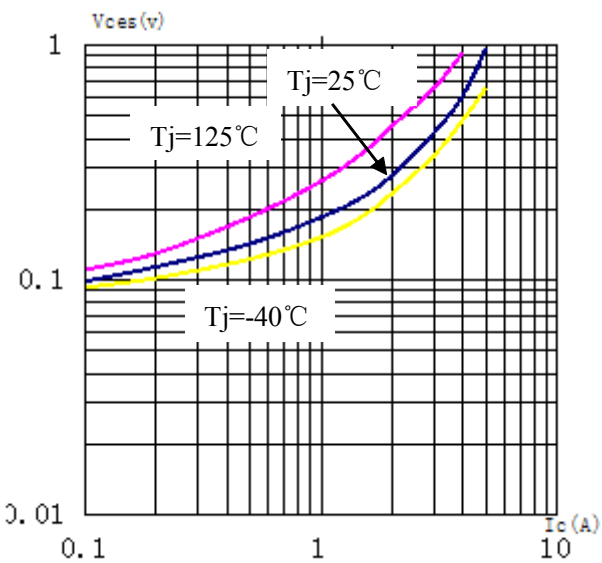
$P_{tot} \propto T_j$



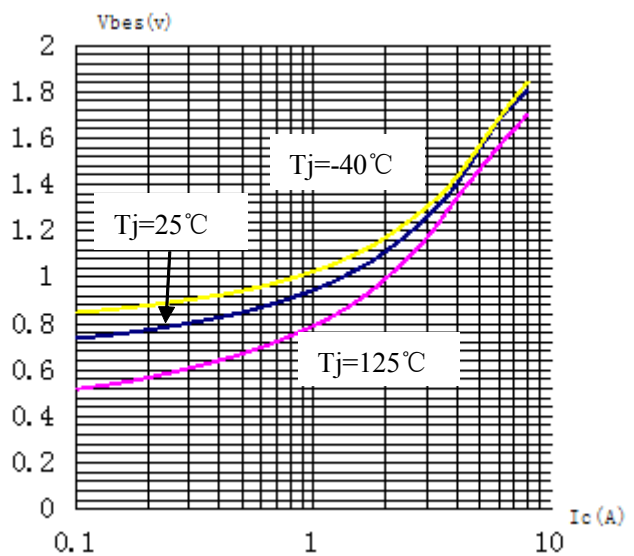
hFE-Ic



Vces-Ic



Vbes-Ic

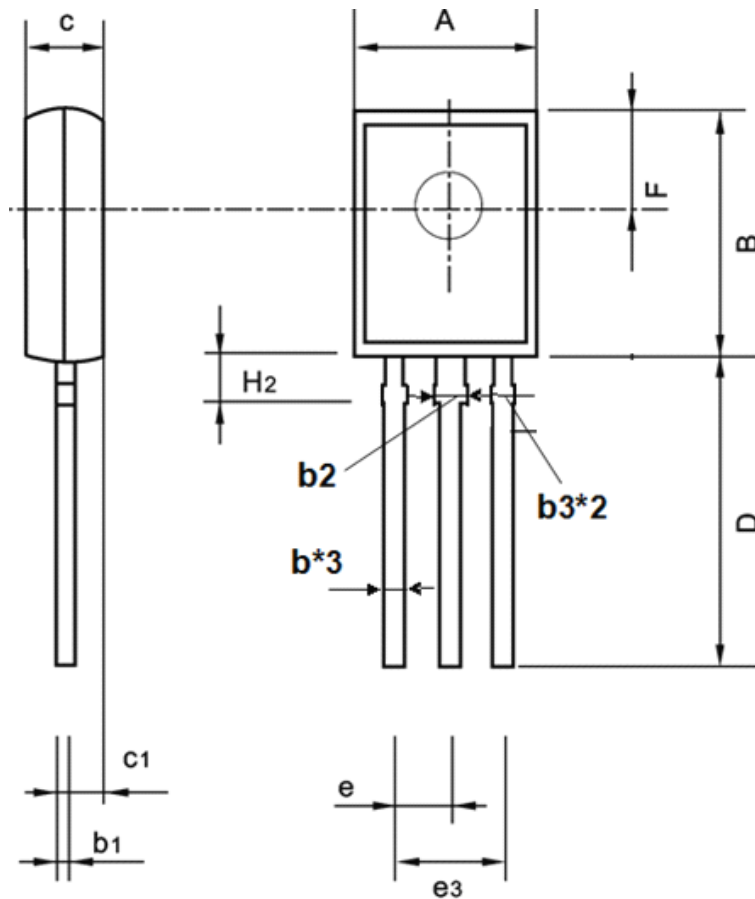




## SOT-82 封装机械尺寸 SOT-82 MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	最小值/min	典型值/nom	最大值/max
A	7.40		7.80
B	10.50		11.10
b	0.70		0.90
b1	0.38		0.60
b2	1.25	1.27	1.35
b3	0.70	0.76	0.90
C	2.40		2.70
c1	1.00		1.30
D	15.00		16.50
e		2.20	
e3	4.15		4.65
F		3.80	
H2		2.15	





### SOT-82S 封装机械尺寸 SOT-82S MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	最小值/min	典型值/nom	最大值/max
A	7.40		7.80
B	10.50		11.10
b	0.70		0.90
b1	0.38		0.60
b2	1.25	1.27	1.35
b3	0.70	0.76	0.90
C	2.40		2.70
c1	1.00		1.30
D	3.20		3.80
e		2.29	
e3	4.15		4.65
F		3.80	
H2			2.40

